

ABSTRACT

A semiconductor laser device 1 has, arranged inside an airtight-sealed package 2, a semiconductor laser element 3 having an active region made of one material selected from the group consisting of an AlGaAs-based crystal, an AlGaInP-based crystal, an AlGaN-based crystal, and an InGaN-based crystal. The atmospheric gas inside the package 2 contains oxygen. The semiconductor laser element 3 has a dielectric oxide film formed on the laser emission surface thereof. The atmospheric gas is a mixture of oxygen and nitrogen, with an oxygen content of 20% or more.